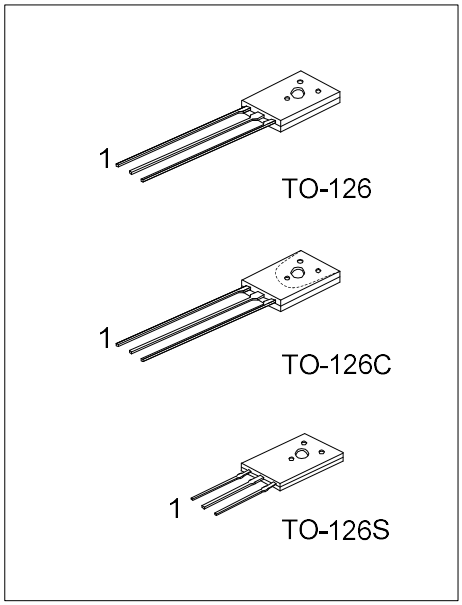
2SC5026

NPN SILICON TRANSISTOR

HIGH VOLTAGE NPN TRANSISTOR



■ DESCRIPTION

Switching Regulator and High Voltage Switching Applications
High-Speed DC-DC Converter Applications.

■ FEATURES

* High collectors breakdown voltage: V_{CEO} = 800V

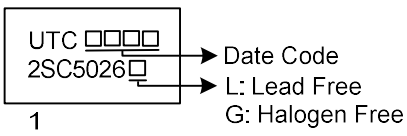
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC5026L-T60-K	2SC5026G-T60-K	TO-126	E	C	B	Bulk
2SC5026L-T6C-K	2SC5026G-T6C-K	TO-126C	E	C	B	Bulk
2SC5026L-T6S-K	2SC5026G-T6S-K	TO-126S	E	C	B	Bulk

Note: Pin Assignment: E: Emitter C: Collector B: Base

2SC5026G-T60-K (1)Packing Type (2)Package Type (3)Green Package	(1) K: Bulk (2) T60: TO-126, T6C: TO-126C, T6S: TO-126S (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	1100	V
Collector-Emitter Voltage		V_{CEO}	800	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	1.5	A
	Pulse	I_{CP}	5	A
Base Current		I_B	0.8	A
Collector Power Dissipation		P_D	20	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	89.3	°C/W
Junction to Case	θ_{JC}	6.25	°C/W

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise specified)

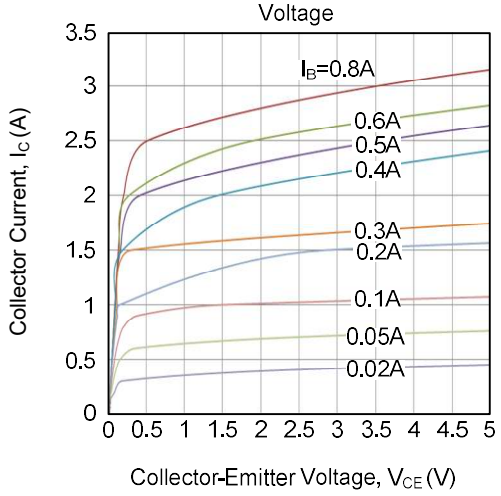
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=1mA, I_E=0	1100			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=5mA, I_B=0	800			V
Emitter−Base Breakdown Voltage	BVEBO	I_E=1mA, I_C=0	7			
Collector Cut-off Current	I_{CBO}	V_{CB}=800V, I_E=0			10	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C= 0			10	μA
DC Current Gain	hFE1	V_{CE}=5V, I_C=0.1A	10		40	
	hFE2	V_{CE}=5V, I_C=0.5A	8			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=0.75A, I_B=0.15A			2	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I_C=0.75A, I_B=0.15A			1.5	V
Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		20		pF
Current Gain Bandwidth Product	f_T	V_{CE}=10V, I_C = 0.1A		15		MHz

■ CLASSIFICATION OF h_{FE1}

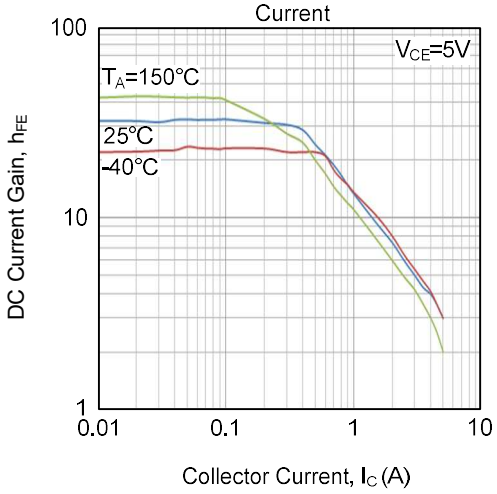
RANK	N	R	O
RANGE	10-20	15-30	20-40

■ TYPICAL CHARACTERISTICS

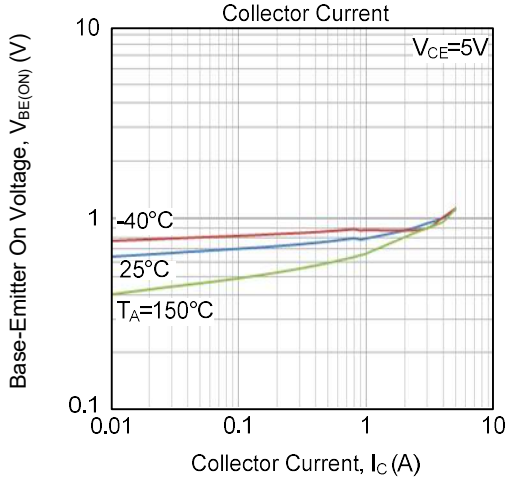
Collector Current vs. Collector-Emitter Voltage



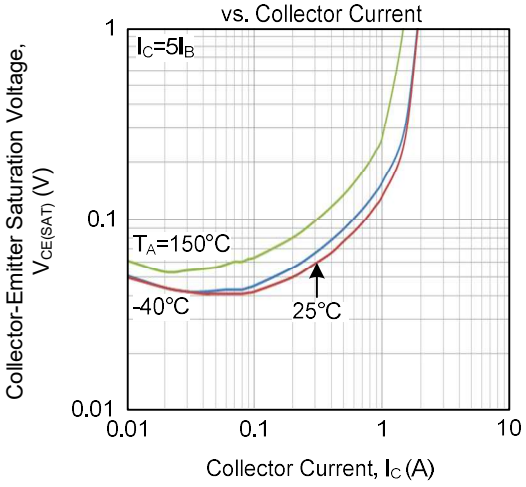
DC Current Gain vs. Collector Current



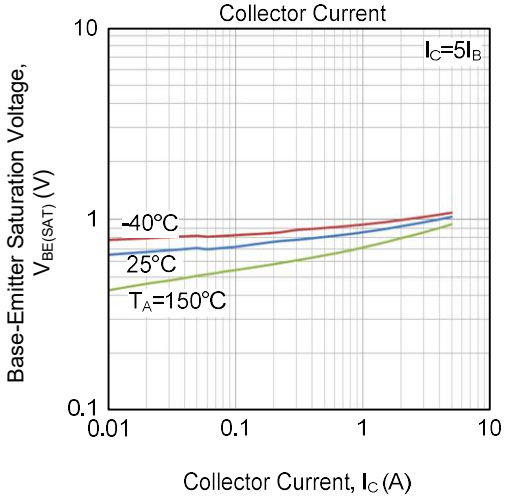
Base-Emitter On Voltage vs. Collector Current



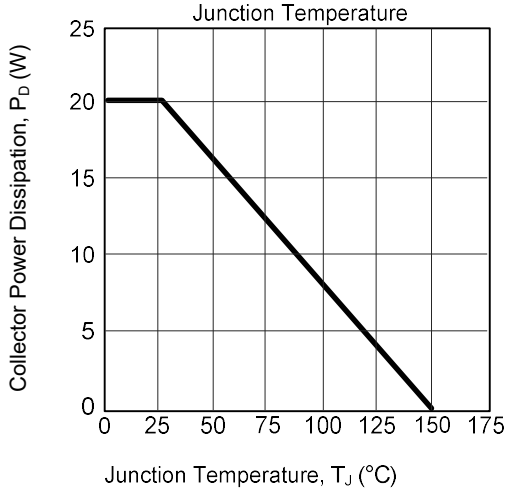
Collector-Emitter Saturation Voltage vs. Collector Current



Base-Emitter Saturation Voltage vs. Collector Current



Collector Power Dissipation vs. Junction Temperature



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